

Notic of R ferenc s Cited	Application/Control No. 10/768,747	Applicant(s)/Patent Under Reexamination PECKERAR ET AL.	
	Examiner Maria Guerrero	Art Unit 2822	Page 1 of 1

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*	B	US-5,847,418 A	12-1998	Nakamura et al.	257/186
*	C	US-5,093,576 A	03-1992	Edmond et al.	250/370.01
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NON-PATENT DOCUMENTS

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	V	Zheleva et al. "Dislocation density reduction via lateral epitaxy in selectively grown GaN structures"; October 1997, Appl. Phys. Lettt.; pages 2472-2474.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.